

## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

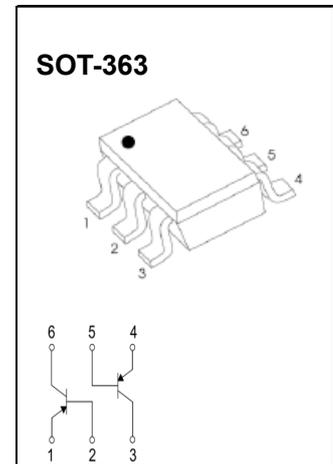
### FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: 3C

MAXIMUM RATINGS( $T_a=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector- Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-45	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.2	A
$P_C$	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	$^\circ\text{C}/\text{W}$
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



### ELECTRICAL CHARACTERISTICS( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	125		630	
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-0.3	V
	$V_{CE(sat)(2)}$	$I_C=-100\text{mA}, I_B=-5\text{mA}$			-0.65	V
Base-emitter voltage	$V_{BE(1)}$	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	-0.6		-0.75	V
	$V_{BE(2)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$			-0.82	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		3.5		pF
Noise figure	NF	$V_{CE}=-5\text{V}, I_C=-0.2\text{mA}, f=1\text{kHz}, R_s=2\text{K}\Omega, BW=200\text{Hz}$		2.5		dB

**Typical Characteristics**
